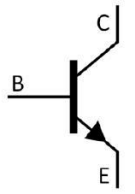
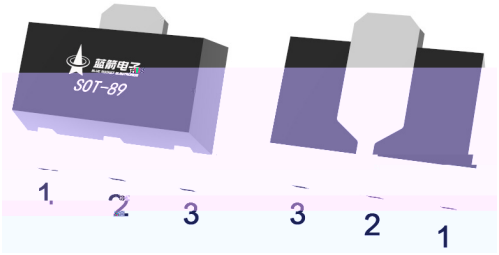
Silicon NPN transistor in a SOT-89 Plastic Package.

High current, low voltage, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

Driver stages of audio and video amplifiers applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit





PIN1 Base PIN 2 Collector PIN 3 Emitter

/ Marking

$h_{FE(1)}$ Classifications	10	16
$h_{FE(1)}$ Range	63 160	100 250

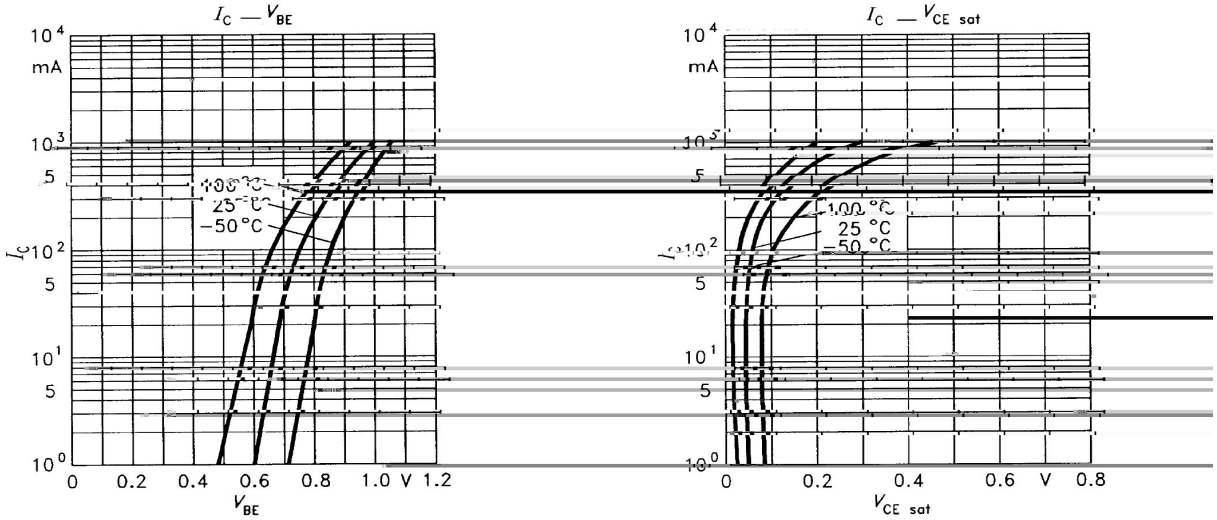
/ Absolute Maximum Ratings(Ta=25)

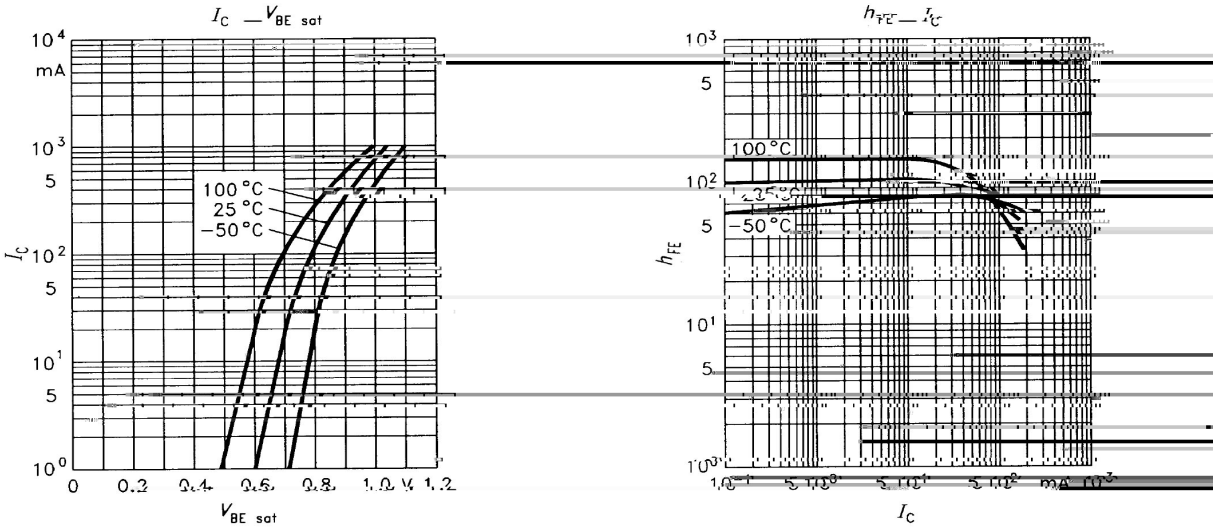
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current-Continuous	I_C	1	A
Peak Collector Current	I_{CM}	1.5	A
Peak Base Current	I_{BM}	0.2	A
Collector Power Dissipation	P_C(T_C=25)	1.3	W
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100 A I_E=0	100			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=500 A I_B=0	80			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100 A I_C=0	5.0			V
Collector Cut-Off Current	$I_{CBO(1)}$	V_{CB}=30V I_E=0			0.1	μA
	$I_{CBO(2)}$	V_{CB}=30V I_E=0 T_j=125			10	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2V I_C=150mA	63		250	
	$h_{FE(2)}$	V_{CE}=2V I_C=5mA	40			
	$h_{FE(3)}$	V_{CE}=2V I_C=500mA	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA I_B=50mA			0.5	V
Base to Emitter Voltage	V_{BE}	I_C=500mA V_{CE}=2V			1	V
Transition Frequency	f_T	I_C=10mA V_{CE}=5V f=100MHz		130		MHz
DC Current Gain Ratio Of The Complementary Pairs	$\frac{h_{FE1}}{h_{FE2}}$	$\|I_C\|$=150mA $\|V_{CE}\|$=2V		1.3	1.6	

/ Electrical Characteristic Curve

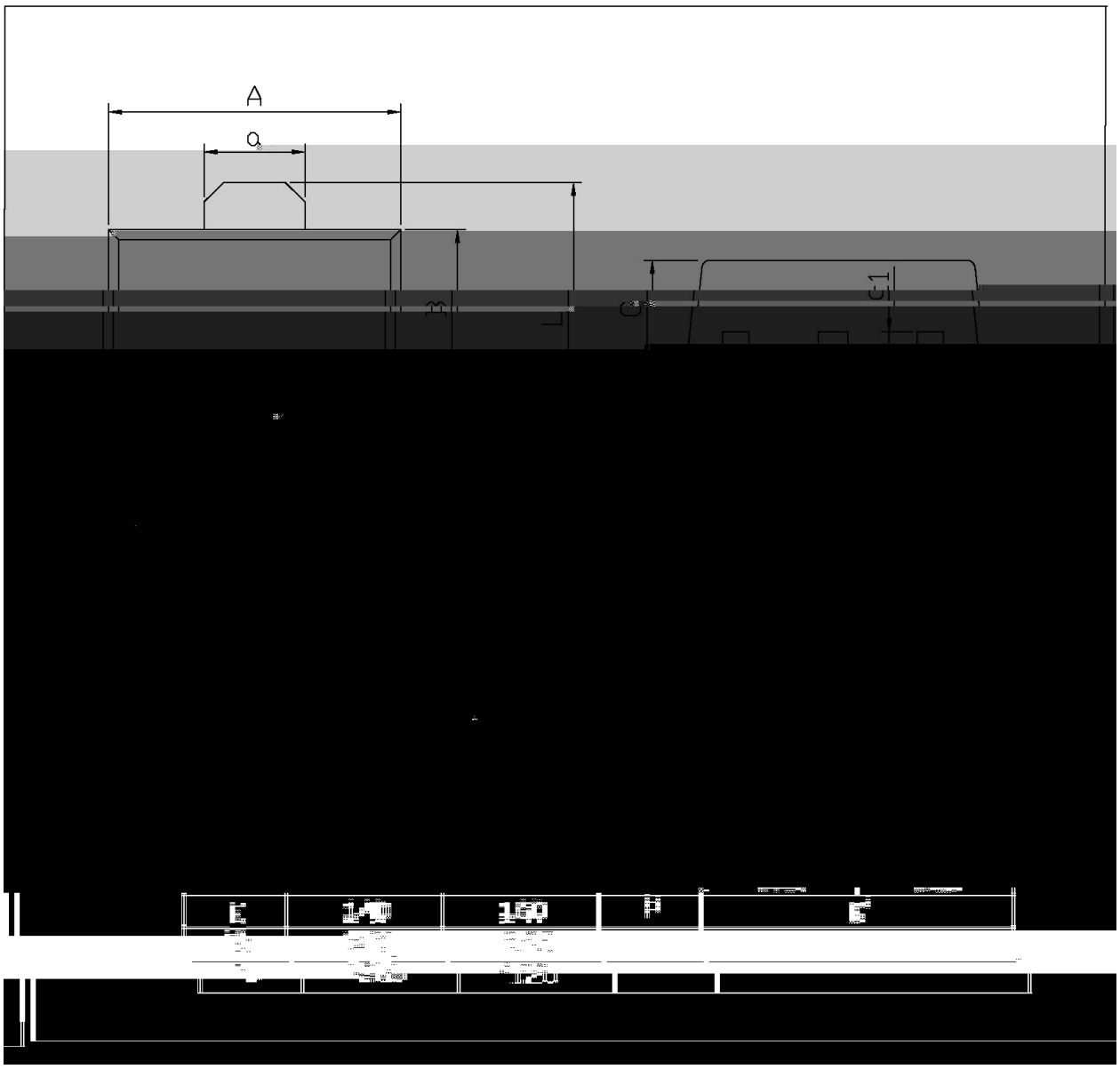




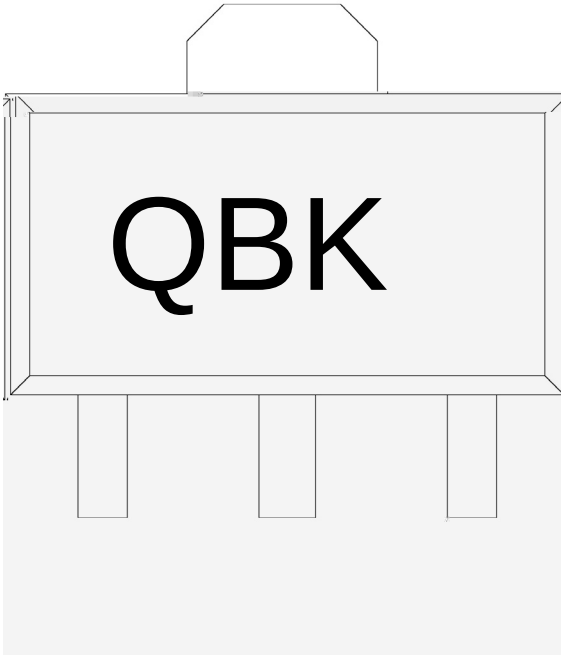
/ Package Dimensions

SOT-89

单位：mm



/ Marking Instructions



BK

Note:

Q: Automobile halogen-free product Code

BK: Product Type

**: Lot No. Code, code change with Lot No